

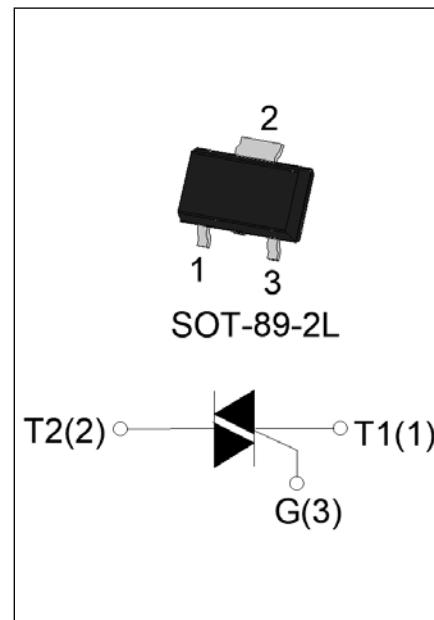


JST131N2-800E 1A TRIAC

Rev.A.1.0

DESCRIPTION:

The JST131N2-800E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Package SOT-89-2L is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(\text{RMS})}$	1	A
$V_{\text{DRM}} / V_{\text{RRM}}$	800	V
$I_{\text{GT}} / / /$	10/10/10/25	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c = 58^\circ\text{C}$)	$I_{T(\text{RMS})}$	1	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	16.5	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		18	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	1.36	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{\text{GT}}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	70	A/s
		40	
Peak gate current ($t_p=20\text{ s}$, $T_j=125^\circ\text{C}$)	I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{\text{G(AV)}}$	0.5	W
Peak gate power	P_{GM}	5	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive,off-state;FIG.8)	V_{PP}	3.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	10	mA
				25	
V_{GT}	ALL		MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	- -	MAX.	15	mA
				30	
I_H	$I_T=50\text{mA}$		MAX.	15	mA
dV/dt	$V_D=540V$ Gate Open $T_j=110^\circ\text{C}$		MIN.	200	V/s
$(dV/dt)c$	$(dI/dt)c=0.44\text{A/ms}$, $T_j=110^\circ\text{C}$		MIN.	6	
t_{on}	$I_G=40\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$	TYP.	3	s	
			30		

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.4\text{A}$ $t_p=380\text{ }\mu\text{s}$	$T_j=25^\circ\text{C}$	1.45	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.96	V
R_D	Dynamic resistance	$T_j=125^\circ\text{C}$	225	
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	A
I_{RRM}		$T_j=125^\circ\text{C}$	0.25	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	50	/W
$R_{th(j-a)}$	junction to ambient ((AC, in free air, $S=5\text{cm}^2$)	100	/W

ORDERING INFORMATION

J	ST	131	N2	-800	E
JieJie Microelectronics Co., Ltd.					
	Triacs				
		IT(RMS):1A			
			N2:SOT-89-2L		
				E:IGT1-3 10mA IGT4 25mA	
					800:V _{DRM} /V _{RRM} 800V

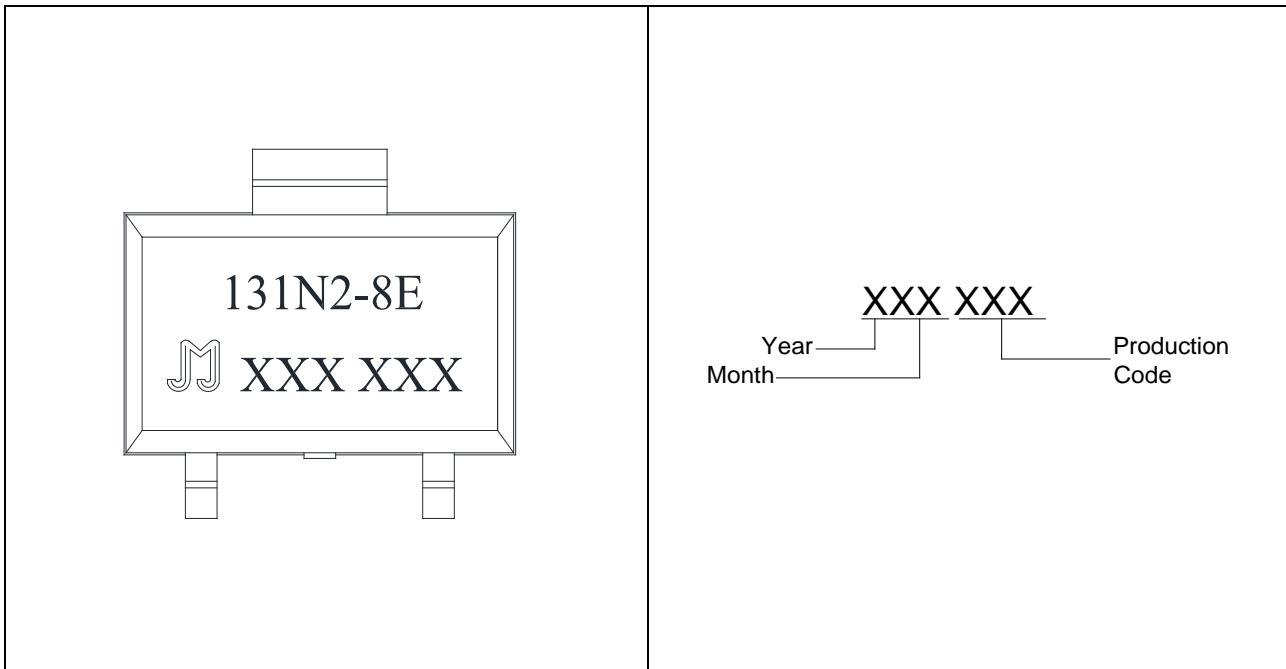
MARKING

FIG.1 Maximum power dissipation versus RMS on-state current

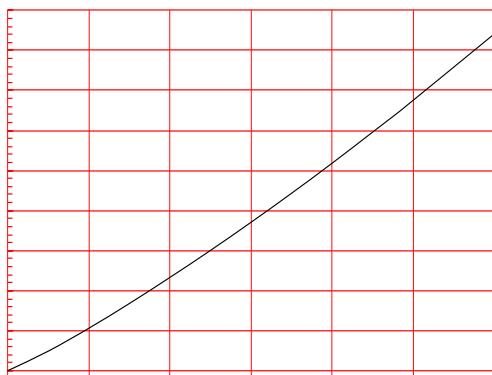


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: (full cycle)



FIG.2: RMS on-state current versus case temperature

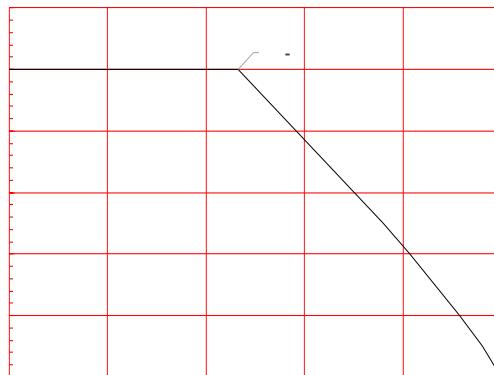


FIG.4: Surge peak on-state current versus number of cycles

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

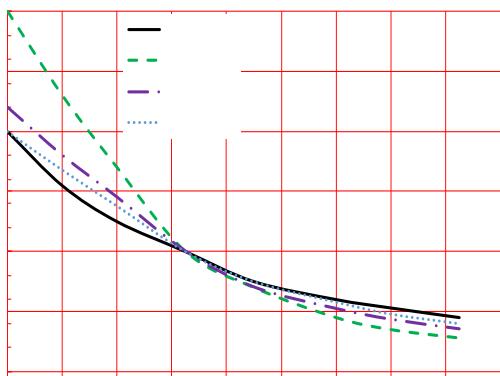
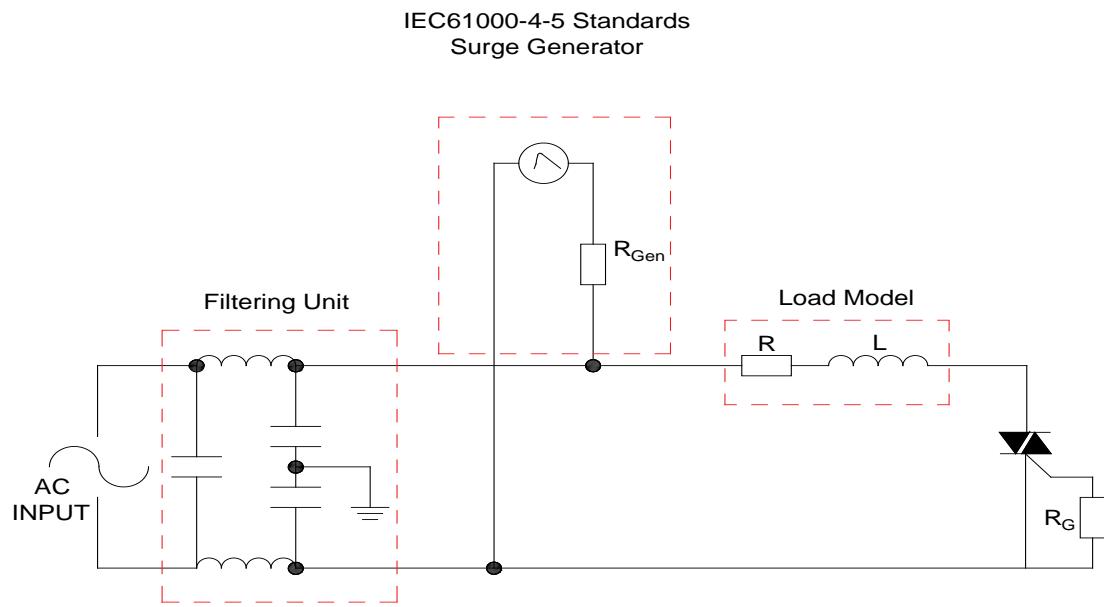


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

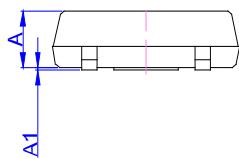


ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		H	I-J			
JST131N2-800E	800	10	25	SOT-89-2L	4,000	Tape & Reel

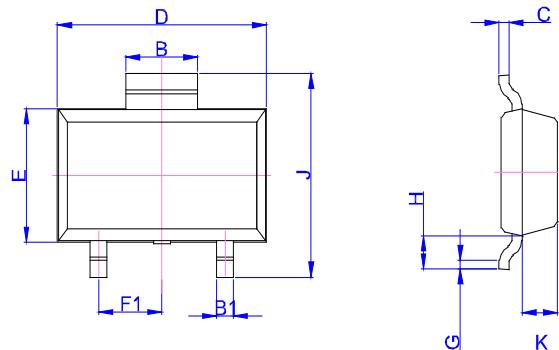
Document Revision History

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA

Dimensions

Ref. Milli m



Dimensions

Ref.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
P2	1.90	2.00	2.10	0.075	0.079	0.082
D	-	1.50	1.60	-	0.059	0.063
D1	1.50			0.059		
P0	3.90	4.00	4.10	0.154	0.157	0.161
10P0	39.80	40.00	40.20	1.567	1.575	1.583
W			12.30			0.482
P	7.90	8.00	8.10	0.311	0.315	0.319
A0	5.20	5.30	5.40	0.204	0.208	0.212
B0	4.80	4.90	5.00	0.188	0.192	0.196
K0	1.75	1.85	1.95	0.069	0.073	0.076
t	0.20	0.25	0.30	0.008	0.010	0.012
			3°		5°	
				3°		5°

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